

(19) World Intellectual Property Organization
International Bureau(43) International Publication Date
22 March 2001 (22.03.2001)

PCT

(10) International Publication Number
WO 01/20691 A1(51) International Patent Classification⁷: H01L 51/30,
H01B 1/12AA Eindhoven (NL). **GELINCK, Gerwin, H.** [NL/NL]; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **TOUWSLAGER, Fredericus, J.** [NL/NL]; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **WILLARD, Nicolaas, P.** [NL/NL]; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).(21) International Application Number: PCT/EP00/08695
(22) International Filing Date:
6 September 2000 (06.09.2000)(74) Agent: **DUIJVESTIJN, Adrianus, J.**; Internationaal Octroibureau B.V., Prof Holstlaan 6, NL-5656 AA Eindhoven (NL).(25) Filing Language: English
(26) Publication Language: English

(81) Designated States (national): JP, US.

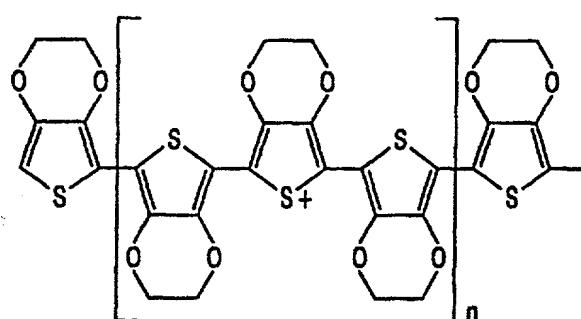
(30) Priority Data:
99202950.4 10 September 1999 (10.09.1999) EP
99203636.8 4 November 1999 (04.11.1999) EP

(84) Designated States (regional): European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

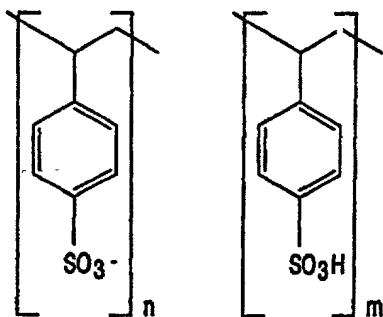
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(54) Title: CONDUCTIVE STRUCTURE BASED ON POLY-3,4-ALKENEDIOXYTHIOPHENE (PEDOT) AND POLYSTYRENE SULFONIC ACID (PSS)



(57) Abstract: An electronic component has an electrically conductive relief structure (3) which contains a salt of a poly-3,4-alkylenedioxythiophene. This salt provides the structure with a stable conductivity. The salt is a polyacid salt by preference. The polyacid salt of poly-3,4-alkylenedioxythiophene is used in the method of manufacturing a relief structure on an electrically insulating substrate. Relief structures (3) comprising tracks (311-314, 321-324) and channels (141) with track widths (tW) and channel lengths (cL) of less than 10 µm can be achieved. The tracks (311-314; 321-324) are used as electrodes (31; 32), the channels (141) are used as semiconductor channels in electronic components, especially in fieldeffect transistors (11) and light-emitting diodes.



WO 01/20691 A1